

Application Number: 09/816,177  
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**APPENDIX TO AMENDMENT OF April 22, 2002**

**Version of Claim with Markings to Show Changes Made**

**AMENDMENTS TO THE CLAIM:**

Please amend claim 1 as follows:

1. (Amended) A semiconductor device comprising:

a Cu film provided above a main surface of a semiconductor substrate and used as a wiring;

an intermediate layer formed at least on the Cu film, the intermediate layer comprising a TaN film formed on the Cu film and a Ta film formed on the TaN film; and

an Al film formed on the [intermediate layer] Ta film and used as a pad[;

wherein the intermediate layer comprises a refractory metal nitride film and a refractory metal film formed on the refractory metal nitride film].



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